
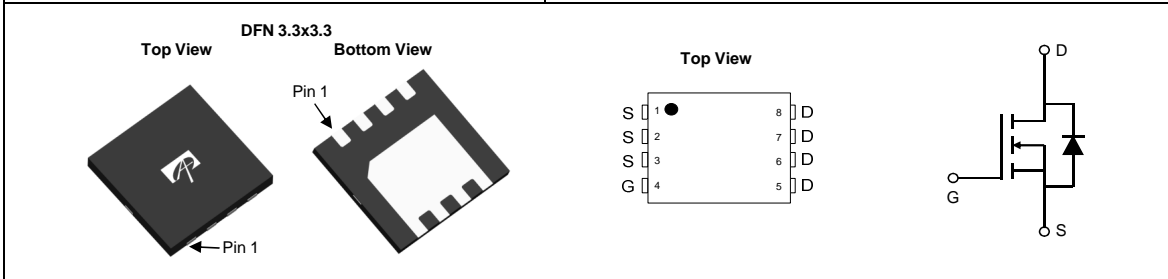


<p><b>General Description</b></p> <ul style="list-style-type: none"> <li>• Latest Trench Power AlphaMOS (αMOS LV) technology</li> <li>• Very Low <math>R_{DS(ON)}</math></li> <li>• Low Gate Charge</li> <li>• High Current Capability</li> <li>• RoHS and Halogen-Free Compliant</li> </ul> <p><b>Application</b></p> <ul style="list-style-type: none"> <li>• System/Load Switchch, Battery Switchch</li> </ul>	<p><b>Product Summary</b></p> <table border="0"> <tr> <td><math>V_{DS}</math></td> <td>30V</td> </tr> <tr> <td><math>I_D</math> (at <math>V_{GS}=10V</math>)</td> <td>75A</td> </tr> <tr> <td><math>R_{DS(ON)}</math> (at <math>V_{GS}=10V</math>)</td> <td>&lt; 1.25mΩ</td> </tr> <tr> <td><math>R_{DS(ON)}</math> (at <math>V_{GS}=4.5V</math>)</td> <td>&lt; 2.1mΩ</td> </tr> </table> <p>100% UIS Tested 100% Rg Tested</p> 	$V_{DS}$	30V	$I_D$ (at $V_{GS}=10V$ )	75A	$R_{DS(ON)}$ (at $V_{GS}=10V$ )	< 1.25mΩ	$R_{DS(ON)}$ (at $V_{GS}=4.5V$ )	< 2.1mΩ
$V_{DS}$	30V								
$I_D$ (at $V_{GS}=10V$ )	75A								
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	< 1.25mΩ								
$R_{DS(ON)}$ (at $V_{GS}=4.5V$ )	< 2.1mΩ								



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AON7510	DFN 3.3x3.3	Tape & Reel	3000

**Absolute Maximum Ratings**  $T_A=25^\circ\text{C}$  unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>G</sup>	$I_D$	$T_C=25^\circ\text{C}$	75
		$T_C=100^\circ\text{C}$	59
Pulsed Drain Current <sup>C</sup>	$I_{DM}$	300	A
Continuous Drain Current	$I_{DSM}$	$T_A=25^\circ\text{C}$	45
		$T_A=70^\circ\text{C}$	35.5
Avalanche Current <sup>C</sup>	$I_{AS}$	60	A
Avalanche energy	$E_{AS}$	90	mJ
$V_{DS}$ Spike	$V_{SPIKE}$	36	V
Power Dissipation <sup>B</sup>	$P_D$	$T_C=25^\circ\text{C}$	46
		$T_C=100^\circ\text{C}$	18.5
Power Dissipation <sup>A</sup>	$P_{DSM}$	$T_A=25^\circ\text{C}$	4.1
		$T_A=70^\circ\text{C}$	2.6
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	25	30	$^\circ\text{C/W}$
Maximum Junction-to-Ambient <sup>A D</sup>		50	60	$^\circ\text{C/W}$
Maximum Junction-to-Case	$R_{\theta JC}$	1.8	2.7	$^\circ\text{C/W}$

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			1 5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.2	1.6	2.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =20A T <sub>J</sub> =125°C		0.9	1.25	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A		1.35	1.85	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =20A		90		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.65	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				58	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz		4500		pF
C <sub>oss</sub>	Output Capacitance			1400		pF
C <sub>riss</sub>	Reverse Transfer Capacitance			1310		pF
R <sub>g</sub>	Gate resistance	f=1MHz	0.9	1.8	2.7	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub> (10V)	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =20A		100	140	nC
Q <sub>g</sub> (4.5V)	Total Gate Charge			60	84	nC
Q <sub>gs</sub>	Gate Source Charge			10		nC
Q <sub>gd</sub>	Gate Drain Charge			40		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, R <sub>L</sub> =0.75Ω, R <sub>GEN</sub> =3Ω		10		ns
t <sub>r</sub>	Turn-On Rise Time			20		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			58		ns
t <sub>f</sub>	Turn-Off Fall Time			37		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =20A, dI/dt=500A/μs		23		ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =20A, dI/dt=500A/μs		49		nC

A. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C. The Power dissipation P<sub>DSM</sub> is based on R<sub>θJA</sub> ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Single pulse width limited by junction temperature T<sub>J(MAX)</sub>=150° C.

D. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to case R<sub>θJC</sub> and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

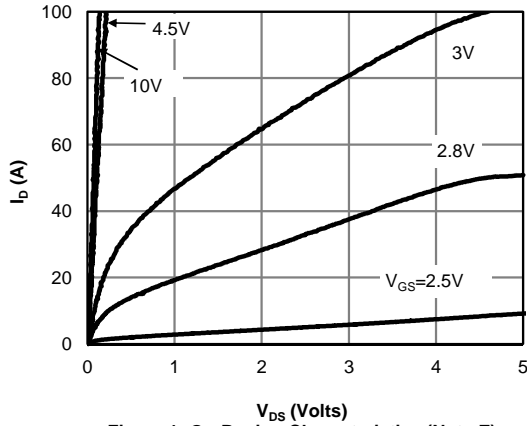
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=150° C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

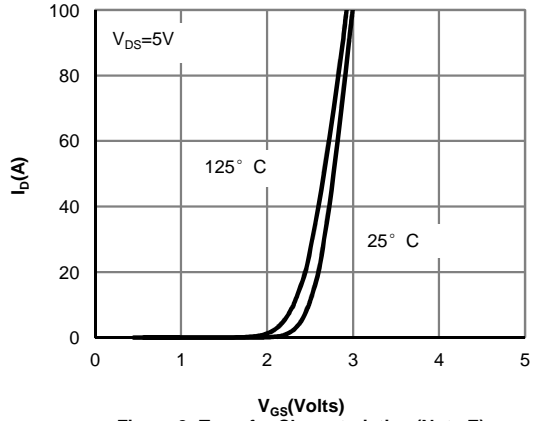
H. These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C.

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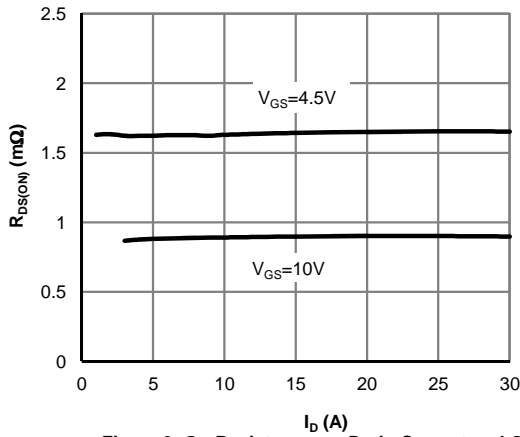
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



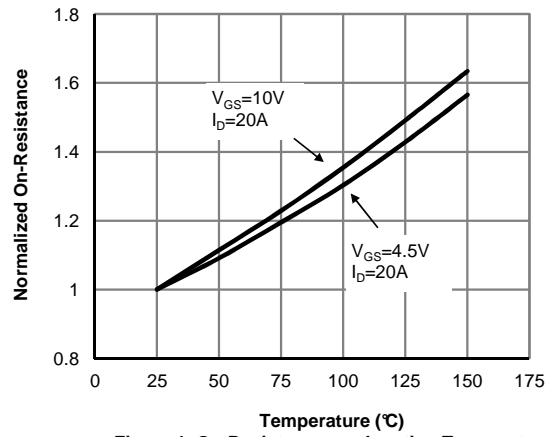
**Figure 1: On-Region Characteristics (Note E)**



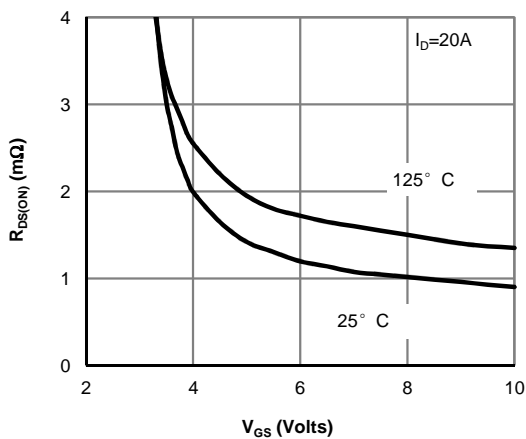
**Figure 2: Transfer Characteristics (Note E)**



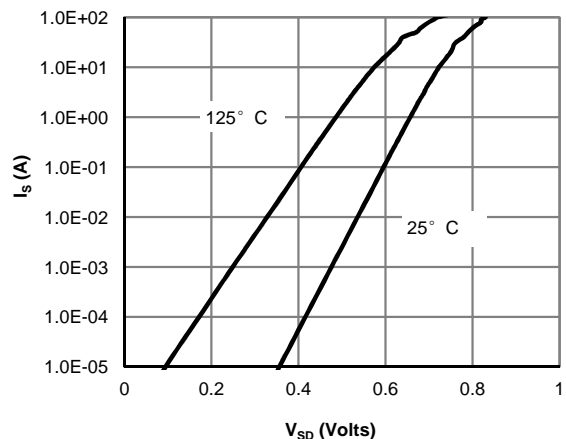
**Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)**



**Figure 4: On-Resistance vs. Junction Temperature (Note E)**



**Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)**



**Figure 6: Body-Diode Characteristics (Note E)**

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

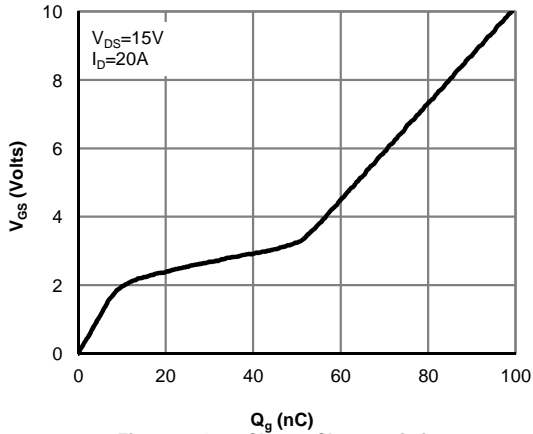


Figure 7: Gate-Charge Characteristics

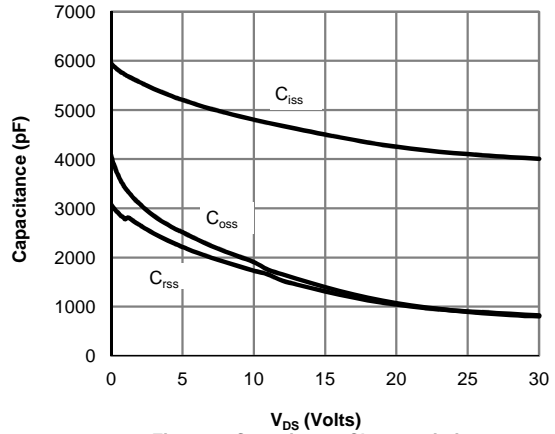


Figure 8: Capacitance Characteristics

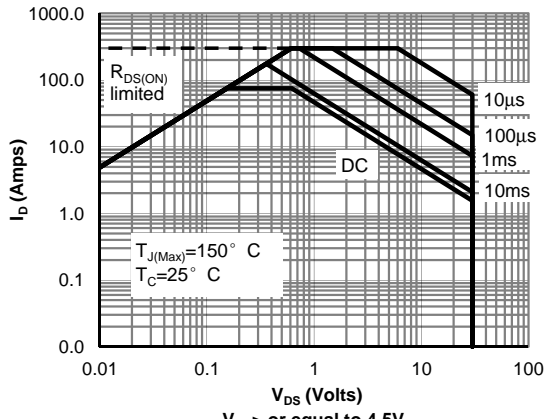


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

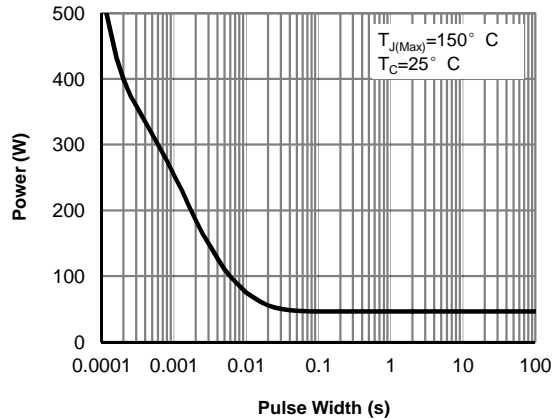


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

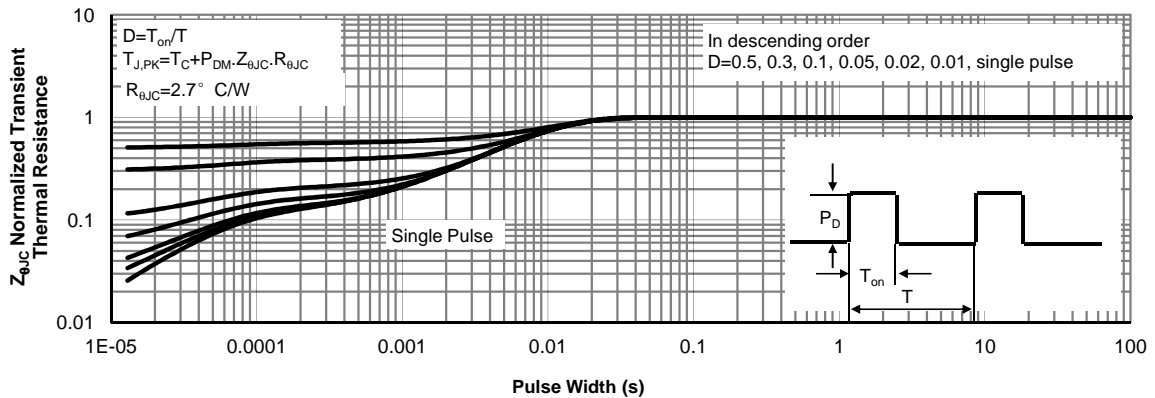


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

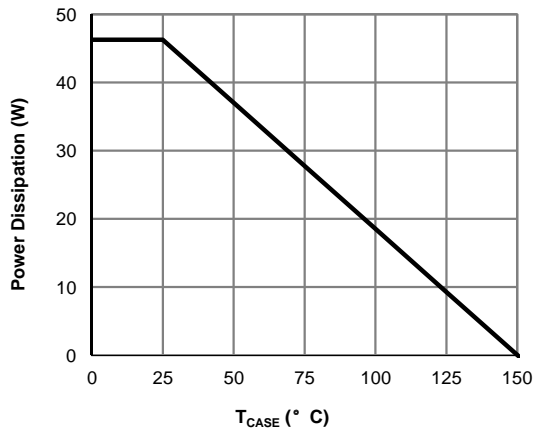


Figure 12: Power De-rating (Note F)

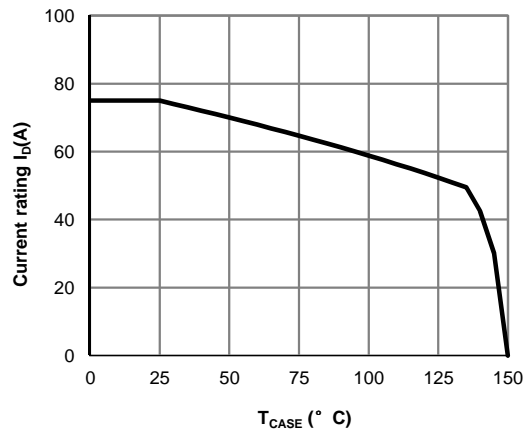


Figure 13: Current De-rating (Note F)

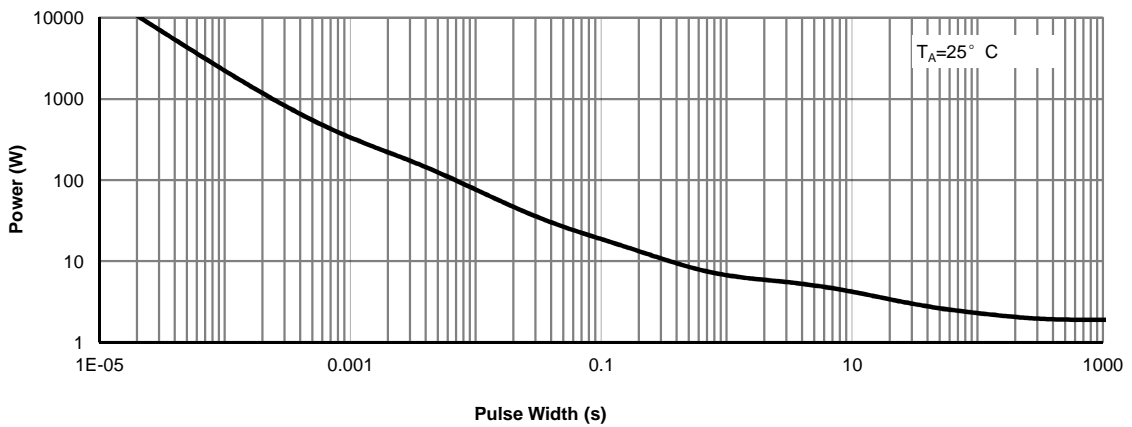


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

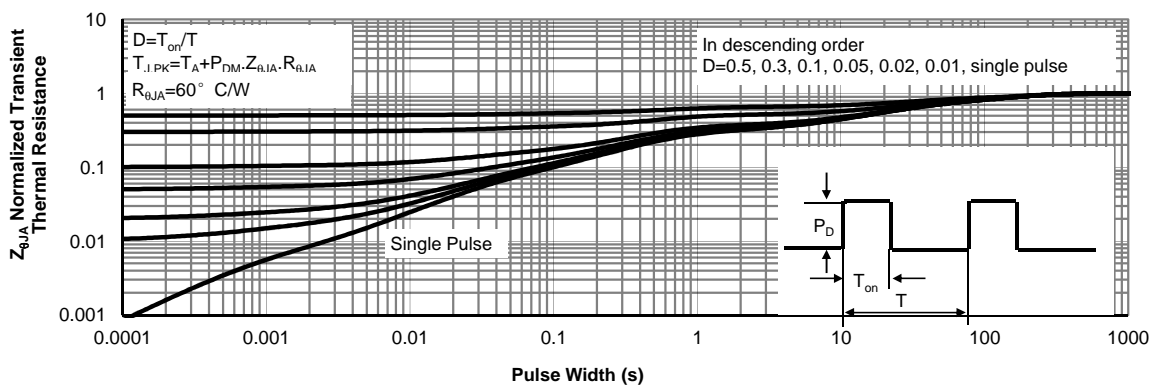
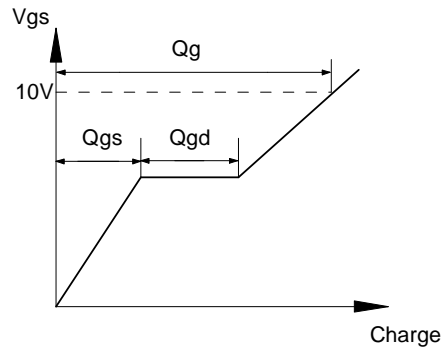
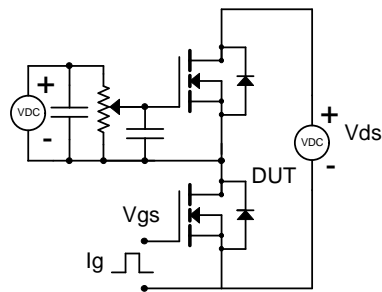
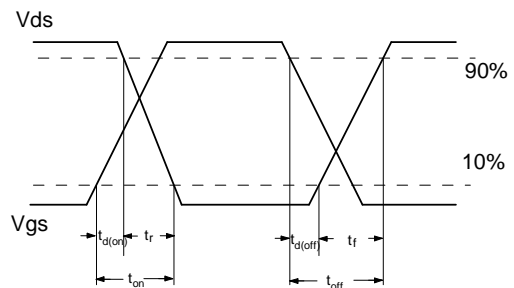
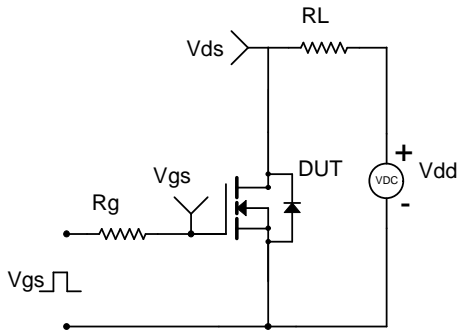


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

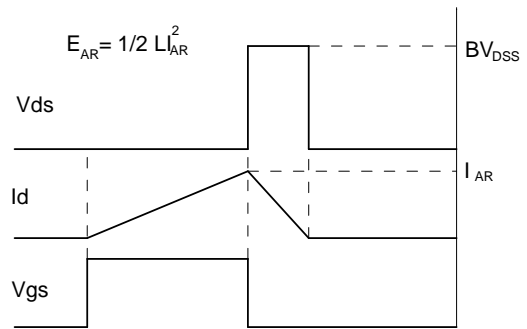
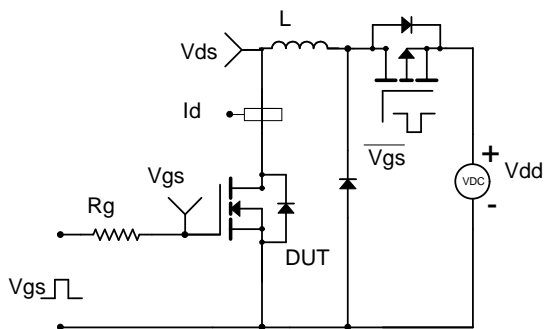
Gate Charge Test Circuit & Waveform



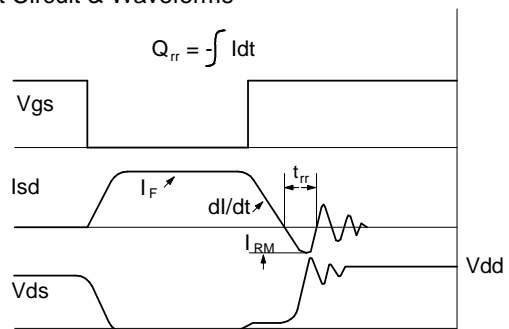
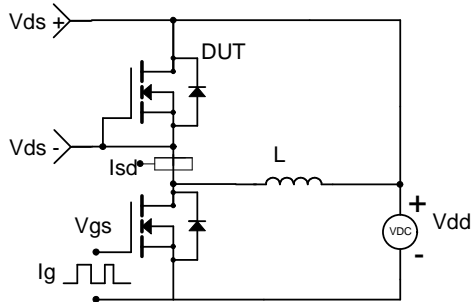
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